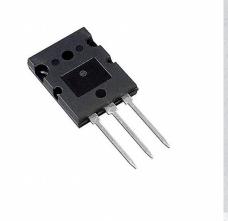


# MJL21193G Datasheet

www.digi-electronics.com



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MJL21193G-DG

Manufacturer onsemi

Manufacturer Product Number MJL21193G

Description TRANS PNP 250V 16A TO264

Detailed Description Bipolar (BJT) Transistor PNP 250 V 16 A 4MHz 200 W

Through Hole TO-264



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MJL21193G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	16 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
250 V	4V @ 3.2A, 16A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100μΑ	25 @ 8A, 5V
Power - Max:	Frequency - Transition:
200 W	4MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-264-3, TO-264AA	TO-264
Base Product Number:	
MJL21193	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):	
ROHS3 Compliant	Not Applicable	
REACH Status:	ECCN:	
REACH Unaffected	EAR99	
HTSUS:		



## **Silicon Power Transistors**

# MJL21193 (PNP), MJL21194 (NPN)

The MJL21193 and MJL21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

#### **Features**

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	250	Vdc
Collector-Base Voltage	$V_{CBO}$	400	Vdc
Emitter-Base Voltage	$V_{EBO}$	5	Vdc
Collector-Emitter Voltage - 1.5 V	$V_{CEX}$	400	Vdc
Collector Current - Continuous	Ic	16	Adc
Collector Current - Peak (Note 1)	I <sub>CM</sub>	30	Adc
Base Current - Continuous	Ι <sub>Β</sub>	5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

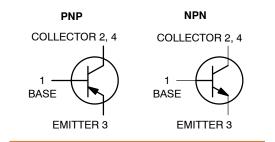
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W

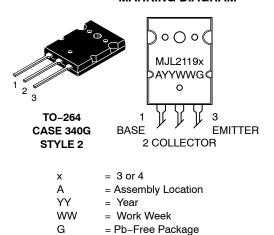
# \*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

1

# 16 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 200 WATTS



#### **MARKING DIAGRAM**



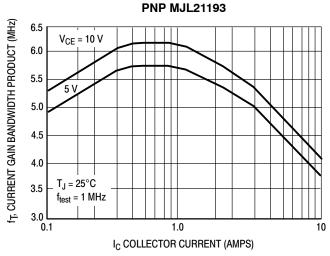
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MJL21193G	TO-264 (Pb-Free)	25 Units / Rail
MJL21194G	TO-264 (Pb-Free)	25 Units / Rail

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector–Emitter Sustaining Voltage ( $I_C = 100 \text{ mAdc}, I_B = 0$ )	V <sub>CEO(sus)</sub>	250	-	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	-	100	μAdc
Emitter Cutoff Current (V <sub>CE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	_	100	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)	I <sub>CEX</sub>	-	-	100	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 1 s (non-repetitive) (V <sub>CE</sub> = 80 Vdc, t = 1 s (non-repetitive)	I <sub>S/b</sub>	4.0 2.25	_ _	_ _	Adc
ON CHARACTERISTICS	•				
DC Current Gain ( $I_C$ = 8 Adc, $V_{CE}$ = 5 Vdc) ( $I_C$ = 16 Adc, $I_B$ = 5 Adc)	h <sub>FE</sub>	25 8	- -	75 -	
Base-Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)	V <sub>BE(on)</sub>	-	-	2.2	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 8$ Adc, $I_B = 0.8$ Adc) ( $I_C = 16$ Adc, $I_B = 3.2$ Adc)	V <sub>CE(sat)</sub>	- -	- -	1.4 4	Vdc
DYNAMIC CHARACTERISTICS					
Total Harmonic Distortion at the Output $V_{RMS}$ = 28.3 V, f = 1 kHz, $P_{LOAD}$ = 100 $W_{RMS}$ unmat	h <sub>FE</sub>		0.8		%
(Matched pair h <sub>FE</sub> = 50 @ 5 A/5 V)	h <sub>FE</sub> ched	_	0.08	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)	f <sub>T</sub>	4	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	-	-	500	pF



6.0 5.0 4.0 3.0 2.0  $T_J = 25^{\circ}C$ 1.0 0.1

NPN MJL21194 f<sub>T</sub>, CURRENT GAIN BANDWIDTH PRODUCT (MHz) 8.0 7.0 10 V V<sub>CE</sub> = 5 V f<sub>test</sub> = 1 MHz 1.0 10 I<sub>C</sub> COLLECTOR CURRENT (AMPS)

Figure 1. Typical Current Gain Bandwidth Product

Figure 2. Typical Current Gain Bandwidth Product

#### **TYPICAL CHARACTERISTICS**

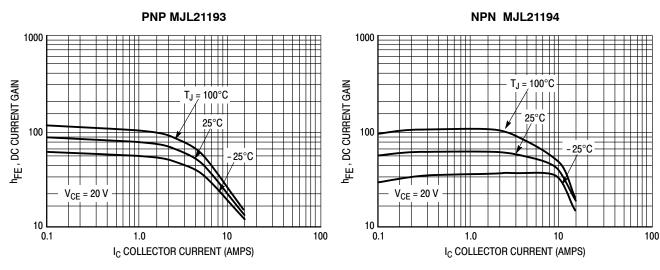


Figure 3. DC Current Gain, V<sub>CE</sub> = 20 V

Figure 4. DC Current Gain, V<sub>CE</sub> = 20 V

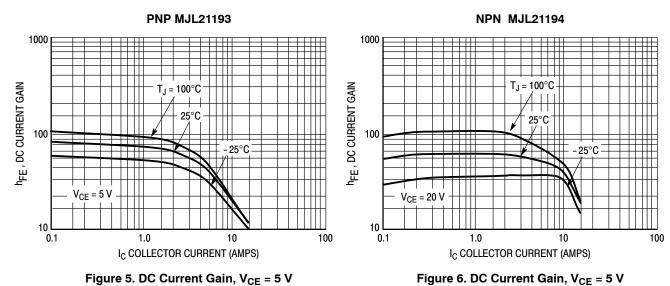


Figure 5. DC Current Gain, V<sub>CE</sub> = 5 V

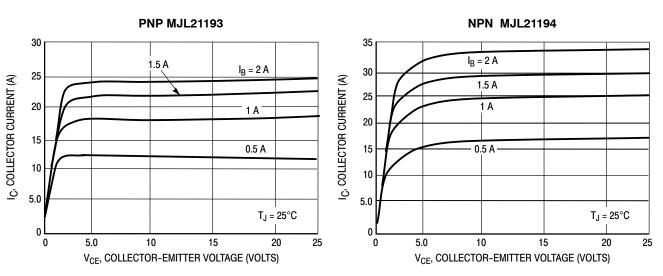


Figure 7. Typical Output Characteristics

Figure 8. Typical Output Characteristics

#### TYPICAL CHARACTERISTICS

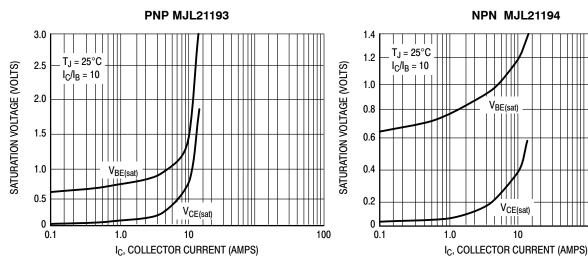


Figure 9. Typical Saturation Voltages

Figure 10. Typical Saturation Voltages

100

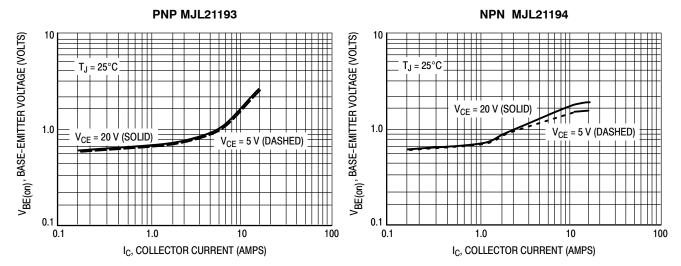


Figure 11. Typical Base-Emitter Voltage

Figure 12. Typical Base-Emitter Voltage

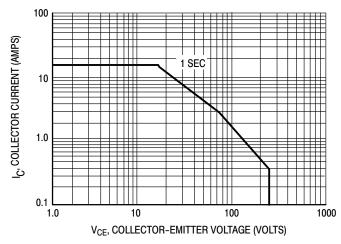


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

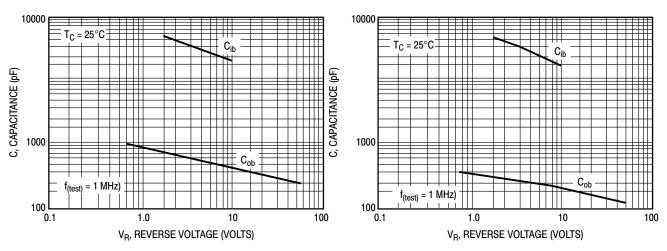


Figure 14. MJL21193 Typical Capacitance

Figure 15. MJL21194 Typical Capacitance

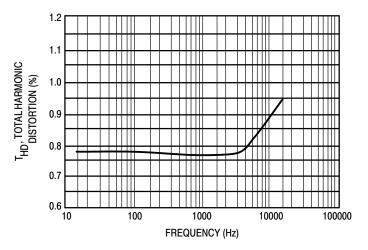


Figure 16. Typical Total Harmonic Distortion

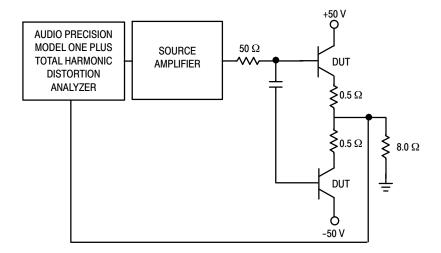
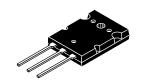


Figure 17. Total Harmonic Distortion Test Circuit



## **MECHANICAL CASE OUTLINE**

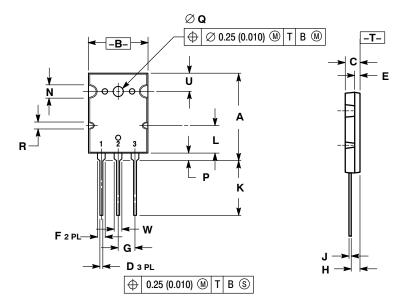
PACKAGE DIMENSIONS



TO-3BPL (TO-264) CASE 340G-02 **ISSUE J** 

**DATE 17 DEC 2004** 

#### SCALE 1:2



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	28.0	29.0	1.102	1.142
В	19.3	20.3	0.760	0.800
С	4.7	5.3	0.185	0.209
D	0.93	1.48	0.037	0.058
E	1.9	2.1	0.075	0.083
F	2.2	2.4	0.087	0.102
G	5.45 BSC		0.215 BSC	
Н	2.6	3.0	0.102	0.118
J	0.43	0.78	0.017	0.031
K	17.6	18.8	0.693	0.740
L	11.2 REF		0.411 REF	
N	4.35 REF		0.172 REF	
P	2.2	2.6	0.087	0.102
Q	3.1	3.5	0.122	0.137
R	2.25 REF		0.089	REF
U	6.3	REF	0.248 REF	
W	2.8	3.2	0.110	0.125

#### **GENERIC MARKING DIAGRAM\***

STYLE 1: PIN 1. GATE 2. DRAIN

SOURCE

STYLE 2: PIN 1. BASE 2. COLLECTOR

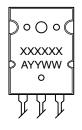
EMITTER

STYLE 3: PIN 1. GATE 2. SOURCE

DRAIN

STYLE 4: PIN 1. DRAIN 2. SOURCE GATE 3.

STYLE 5: PIN 1. GATE 2. COLLECTOR EMITTER



XXXXXX = Specific Device Code

Α = Location Code

YY = Year WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42780B	Electronic versions are uncontrolled except when accessed directly from the Document Reposition Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-3BPL (TO-264)		PAGE 1 OF 1	

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